



Up to 6 GHz Low Noise Silicon Bipolar Transistor

Technical Data

AT-41485

Features

- **Low Noise Figure:**
1.4 dB Typical at 1.0 GHz
1.7 dB Typical at 2.0 GHz
- **High Associated Gain:**
18.5 dB Typical at 1.0 GHz
13.5 dB Typical at 2.0 GHz
- **High Gain-Bandwidth**
Product: 8.0 GHz Typical f_T

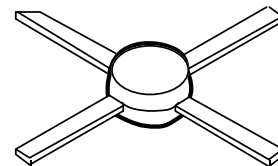
Description

Agilent's AT-41485 is a general purpose NPN bipolar transistor that offers excellent high frequency performance. The AT-41485 is housed in a low cost .085" diameter plastic package. The 4 micron emitter-to-emitter pitch enables this transistor to be used in many different functions. The 14 emitter finger interdigitated geometry yields an interme-

mediate sized transistor with impedances that are easy to match for low noise and moderate power applications. Applications include use in wireless systems as an LNA, gain stage, buffer, oscillator, and mixer. An optimum noise match near 50Ω at 900 MHz, makes this device easy to use as a low noise amplifier.

The AT-41485 bipolar transistor is fabricated using Agilent's 10 GHz f_T Self-Aligned-Transistor (SAT) process. The die is nitride passivated for surface protection. Excellent device uniformity, performance and reliability are produced by the use of ion-implantation, self-alignment techniques, and gold metalization in the fabrication of this device.

85 Plastic Package



AT-41485 Absolute Maximum Ratings

Symbol	Parameter	Units	Absolute Maximum ^[1]
V _{EBO}	Emitter-Base Voltage	V	1.5
V _{CBO}	Collector-Base Voltage	V	20
V _{CEO}	Collector-Emitter Voltage	V	12
I _C	Collector Current	mA	60
P _T	Power Dissipation ^[2,3]	mW	500
T _j	Junction Temperature	°C	150
T _{STG}	Storage Temperature	°C	-65 to 150

Thermal Resistance^[2,4]:

$$\theta_{jc} = 155^{\circ}\text{C/W}$$

Notes:

1. Permanent damage may occur if any of these limits are exceeded.
2. T_{CASE} = 25°C.
3. Derate at 6.5 mW/°C for T_C > 73°C.
4. See MEASUREMENTS section "Thermal Resistance" for more information.

Electrical Specifications, T_A = 25°C

Symbol	Parameters and Test Conditions	Units	Min.	Typ.	Max.
S _{21E} ²	Insertion Power Gain; V _{CE} = 8 V, I _C = 25 mA	f = 1.0 GHz f = 2.0 GHz	dB	17.5 11.5	
P _{1dB}	Power Output @ 1 dB Gain Compression V _{CE} = 8 V, I _C = 25 mA	f = 2.0 GHz	dBm	18.5	
G _{1dB}	1 dB Compressed Gain; V _{CE} = 8 V, I _C = 25 mA	f = 2.0 GHz	dB	14.0	
NF _O	Optimum Noise Figure; V _{CE} = 8 V, I _C = 10 mA	f = 1.0 GHz f = 2.0 GHz f = 4.0 GHz	dB	1.4 1.7 3.0	1.8
G _A	Gain @ NF _O ; V _{CE} = 8 V, I _C = 10 mA	f = 1.0 GHz f = 2.0 GHz f = 4.0 GHz	dB	17.5 18.5 13.5 9.5	
f _T	Gain Bandwidth Product; V _{CE} = 8 V, I _C = 25 mA		GHz	8.0	
h _{FE}	Forward Current Transfer Ratio; V _{CE} = 8 V, I _C = 10 mA		—	30	270
I _{CBO}	Collector Cutoff Current; V _{CB} = 8 V		μA		0.2
I _{EBO}	Emitter Cutoff Current; V _{EB} = 1 V		μA		1.0
C _{CB}	Collector Base Capacitance ^[1] ; V _{CB} = 8 V, f = 1 MHz		pF	0.25	

Notes:

1. For this test, the emitter is grounded.

AT-41485 Typical Performance, $T_A = 25^\circ\text{C}$

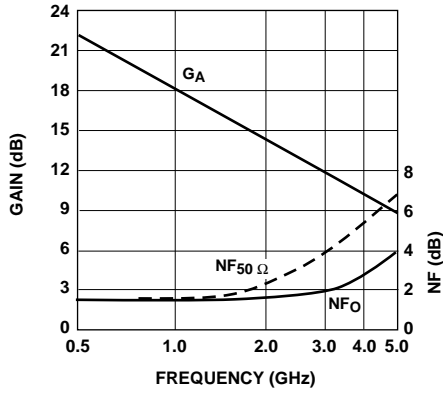


Figure 1. Noise Figure and Associated Gain vs. Frequency.
 $V_{CE} = 8\text{ V}$, $I_C = 10\text{ mA}$.

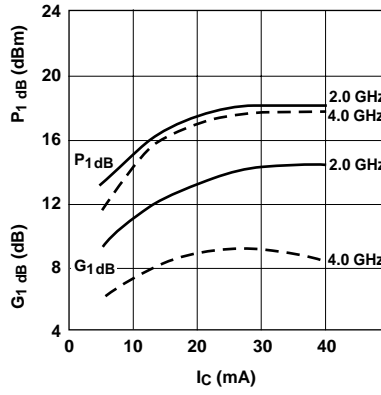


Figure 2. Output Power and 1 dB Compressed Gain vs. Collector Current and Frequency. $V_{CE} = 8\text{ V}$.

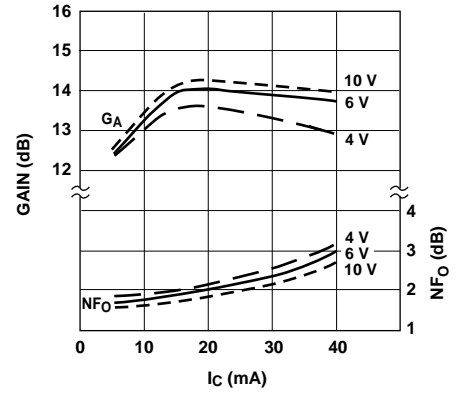


Figure 3. Optimum Noise Figure and Associated Gain vs. Collector Current and Collector Voltage. $f = 2.0\text{ GHz}$.

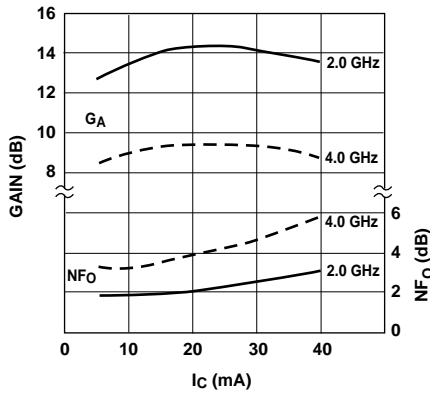


Figure 4. Optimum Noise Figure and Associated Gain vs. Collector Current and Frequency. $V_{CE} = 8\text{ V}$.

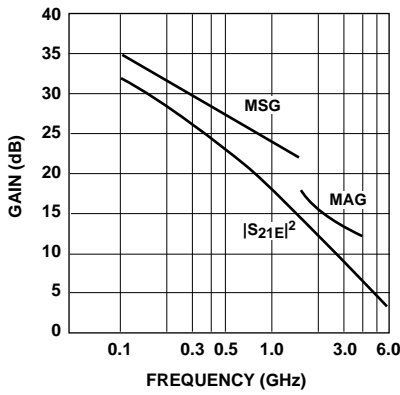


Figure 5. Insertion Power Gain, Maximum Available Gain and Maximum Stable Gain vs. Frequency.
 $V_{CE} = 8\text{ V}$, $I_C = 25\text{ mA}$.

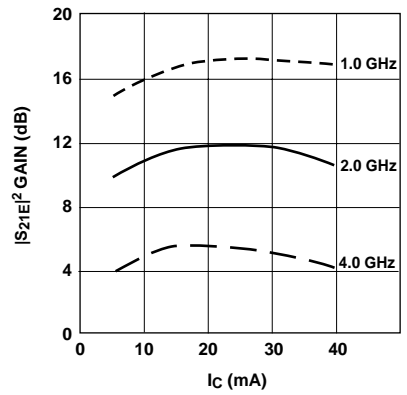


Figure 6. Insertion Power Gain vs. Collector Current and Frequency.
 $V_{CE} = 8\text{ V}$.

AT-41485 Typical Scattering Parameters, Common Emitter, $Z_O = 50 \Omega$, $T_A = 25^\circ\text{C}$, $V_{CE} = 8 \text{ V}$, $I_C = 10 \text{ mA}$

Freq. GHz	S_{11}		dB	S_{21}		dB	S_{12}		S_{22}	
	Mag.	Ang.		Mag.	Ang.		Mag.	Ang.	Mag.	Ang.
0.1	.74	-40	28.2	25.80	156	-35.6	.017	81	.93	-14
0.5	.61	-126	21.9	12.46	108	-29.2	.035	44	.57	-31
1.0	.57	-161	16.6	6.80	87	-27.9	.040	38	.46	-33
1.5	.57	-180	13.4	4.67	75	-25.7	.052	47	.43	-34
2.0	.58	166	11.0	3.55	64	-24.5	.060	54	.41	-38
2.5	.59	160	9.3	2.92	59	-23.3	.068	58	.40	-39
3.0	.61	150	7.7	2.42	50	-21.9	.080	63	.39	-46
3.5	.62	142	6.4	2.09	41	-20.8	.091	61	.41	-54
4.0	.62	134	5.3	1.84	32	-19.5	.106	59	.42	-62
4.5	.62	125	4.3	1.65	24	-18.4	.120	57	.43	-67
5.0	.63	115	3.5	1.50	15	-17.2	.138	54	.44	-73
5.5	.65	103	2.7	1.37	6	-16.1	.157	49	.43	-78
6.0	.69	92	1.8	1.24	-4	-15.3	.172	46	.40	-86

AT-41485 Typical Scattering Parameters, Common Emitter, $Z_O = 50 \Omega$, $T_A = 25^\circ\text{C}$, $V_{CE} = 8 \text{ V}$, $I_C = 25 \text{ mA}$

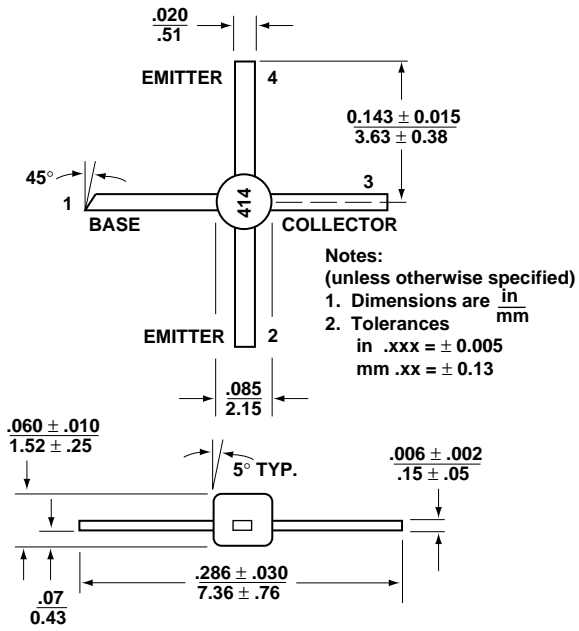
Freq. GHz	S_{11}		dB	S_{21}		dB	S_{12}		S_{22}	
	Mag.	Ang.		Mag.	Ang.		Mag.	Ang.	Mag.	Ang.
0.1	.55	-68	32.0	40.01	146	-40.9	.009	57	.85	-19
0.5	.58	-153	23.1	14.20	99	-32.7	.023	52	.47	-29
1.0	.58	-177	17.4	7.39	82	-29.8	.032	63	.41	-28
1.5	.58	169	14.0	5.01	71	-27.3	.043	60	.39	-30
2.0	.60	158	11.6	3.78	61	-24.6	.059	64	.38	-36
2.5	.60	153	9.8	3.09	58	-23.7	.065	71	.36	-39
3.0	.63	147	8.1	2.55	48	-21.7	.082	68	.35	-47
3.5	.64	140	6.9	2.21	39	-20.7	.092	67	.37	-56
4.0	.64	133	5.8	1.94	31	-19.4	.107	65	.39	-64
4.5	.64	125	4.8	1.74	23	-18.1	.125	63	.40	-71
5.0	.64	115	4.0	1.58	14	-17.1	.140	56	.41	-78
5.5	.66	105	3.2	1.45	5	-15.9	.160	50	.40	-82
6.0	.70	94	2.4	1.32	-5	-15.1	.175	47	.37	-91

A model for this device is available in the DEVICE MODELS section.

AT-41485 Noise Parameters: $V_{CE} = 8 \text{ V}$, $I_C = 10 \text{ mA}$

Freq. GHz	NF_O dB	Γ_{opt}		$R_N/50$
		Mag	Ang	
0.1	1.3	.12	5	0.17
0.5	1.3	.10	25	0.17
1.0	1.4	.06	50	0.16
2.0	1.7	.25	172	0.16
4.0	3.0	.48	-131	0.24

85 Plastic Package Dimensions





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